**Product data sheet** 

## 1. General description

EEPP<sup>™</sup>- Efficiency Enhanced Pt Planar rectifier in a 2-lead TO220-2L plastic package.

### 2. Features and benefits

- · Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- · Soft recovery characteristics
- Low thermal resistance
- · Low leakage current
- · Planar termination structure
- High operating temperature capability (T<sub>j(max)</sub> = 175°C)
- Higher I<sub>FSM</sub> capability

# 3. Applications

- · Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Values			Unit	
Absolute maximum rating								
$V_{RRM}$	repetitive peak reverse voltage			1200			V	
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 120$ °C; Fig. 1; Fig. 2; Fig. 3	8			А		
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 120 °C; square-wave pulse	16			А		
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100			А		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	110		А			
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static ch	aracteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		2.2	2.8	3.2	V	
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	2.2	-	V	
Dynamic	characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	-	55	ns	
Avalanch	Avalanche energy							
E <sub>AS</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		20	-	-	mJ	

**WeEn Semiconductors** 

**BYC8-1200P** 

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K 1/1 A
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod	E A	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC8-1200P	TO220-2L	BYC8-1200PQ	Tube	50	TO220E-2L (E)	26-May-2017
					SOD59 (A)	27-Nov-2012

# 7. Marking

### Table 4. Marking codes

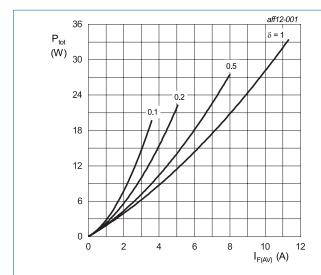
Type number	Marking codes		
	Assembly factory: E	Assembly factory: A	
BYC8-1200P	BYC8 1200P PJExxxx xx	BYC8 1200P PJAxxxx xx	

# 8. Limiting values

#### **Table 5. Limiting values**

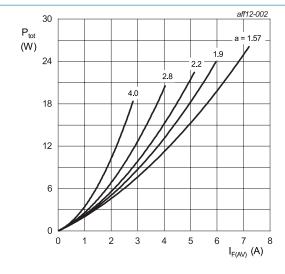
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		1250	V
$V_{\text{RWM}}$	crest working reverse voltage		1250	V
$V_R$	reverse voltage	DC	1250	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 120 °C; Fig. 1; Fig. 2; Fig. 3	8	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 120 °C$ ; square-wave pulse	16	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	110	А
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.768 \text{ V; } R_{\text{s}} = 0.1043 \text{ } \Omega \end{split}$$

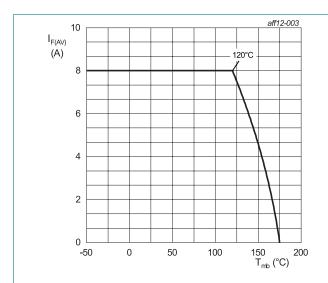
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

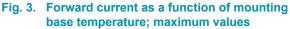


a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.768 V;  $R_s$  = 0.1043  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode





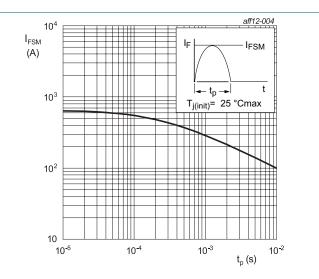


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

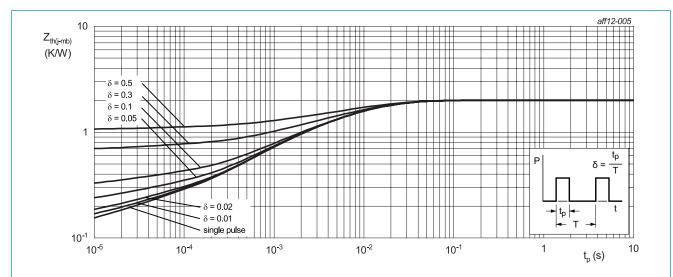


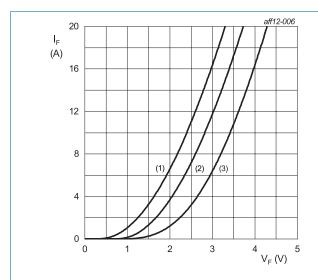
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V <sub>F</sub> f	forward current	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	2.2	2.8	3.2	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	2.2	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-	-	100	μΑ
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 150 °C	-	-	0.5	mA
Dynamic	characteristics			,		
$Q_r$	reverse charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	215	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	475	-	nC
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	525	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	-	55	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	46	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	85	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	90	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	9.2	-	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	11.2	-	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	12	-	А
Avalanc	he energy		'			
E <sub>AS</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C	20	-	-	mJ

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 $V_o$  = 1.768 V;  $R_s$  = 0.1043  $\Omega$ 

(1)  $T_j = 150$  °C; typical values (2)  $T_j = 150$  °C; maximum values

(3) T<sub>j</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

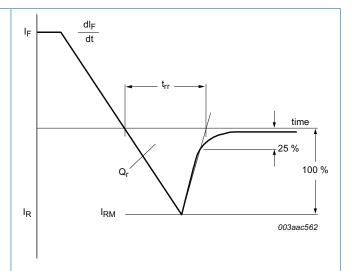
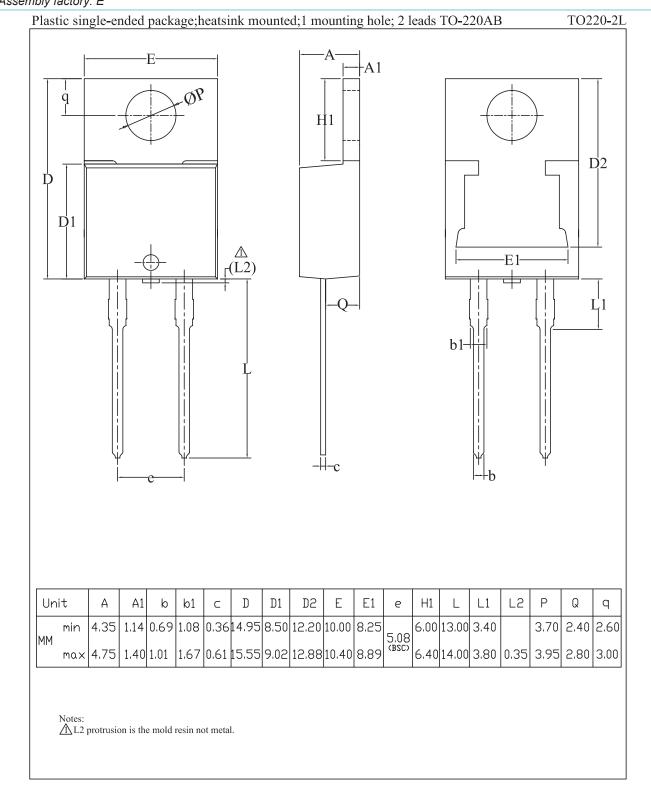


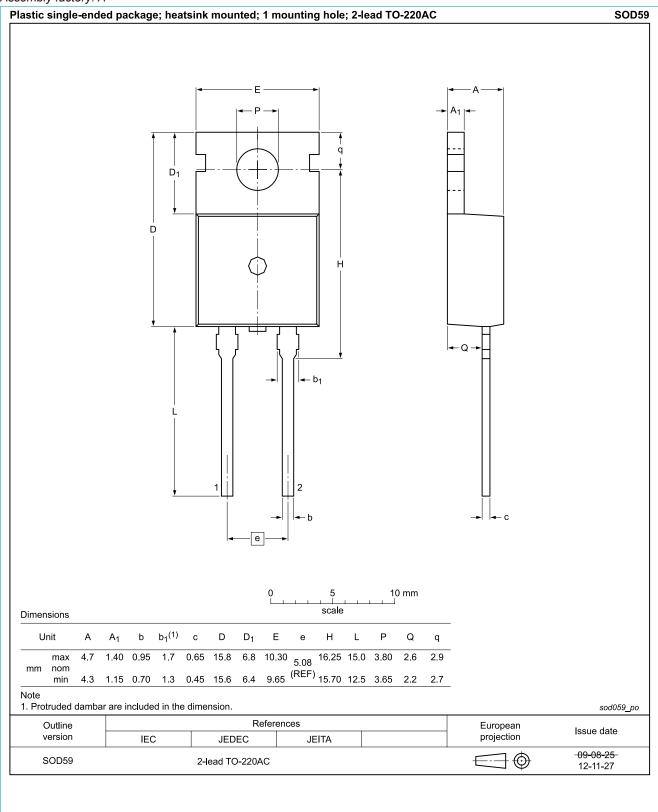
Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline

Assembly factory: E



#### Assembly factory: A



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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